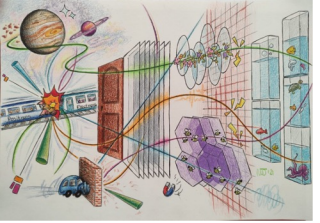


# WP4 - TCAD simulations

## Proposal for workplan and milestones

J. Schwandt, M. Bomben, F. Moscatelli, A. Morozzi,

on behalf of the WP4 preparation/proposal group



## Technology Computer-Aided Design (TCAD):

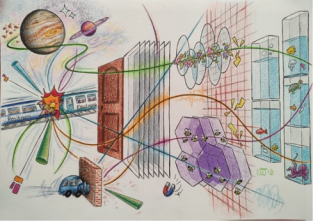
- Is a decisive tool for the detector community for the:
  - Sensor designs and optimization
  - Radiation damage understanding and modeling
  - Electrical field calculation for Monte-Carlo tools
  - Is integral part of full detector system simulation (ATLAS,CMS)
- Mainly commercially available (Synopsys TCAD, Silvaco TCAD)

## Companies implement device physics in different ways:

- Cross calibration required, partially performed for Synopsys and Silvaco TCAD

## Protocols to transfer electric field from TCAD to Monte-Carlo tools:

- Ready for Allpix2

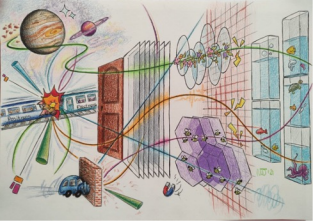


## TCAD as part of full detector simulation:

- **LHC Run1/2/3 pixel detectors:**
  - Both ATLAS and CMS rely on TCAD simulations to include radiation damage effects into their Monte-Carlo simulated events
  - The model used is based on EVL 2 traps one
  - M. Swartz and colleagues expanded it over the years
  - It is now validated on testbeam data till  $2.4e15$ , on collision data till  $\sim 1e15$
- **HL-LHC i.e. fluence  $>\sim 3e15$ :**
  - Perugia model (includes surface damage - see next talk)
  - HPTM
  - LHCb model (developed on irradiated Velo pixels modules, till  $8e15$ )
- **e+e- machines**
  - Surface damage -> Perugia model

## Outreach/Training:

- Europractice Training Course
- Biannual TCAD school SIMDET



## Charge collection time optimization

- 2D and 3D sensors

## Implementation and validation of physics models of non Si materials

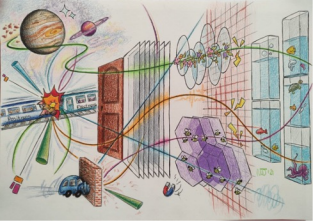
- Focus on SiC, GaN, diamond (?)

## Cluster defect simulation in TCAD

- Occupation-dependent ionization energy
- NIEL scaling

## Further development of physics models:

- Fluence dependence of the IR absorption length
- Effects of mobility reduction due to scattering by ionised defects at high fluences
- Impact-ionisation via local-level at high fluences



# Cooperation with TCAD companies DRD3

## Silvaco

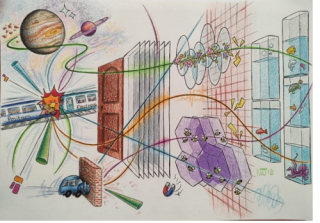
- fruitful interaction since years with engineers
- open/eager to discuss new physics models to be implemented
- support for missing/wanted features (e.g. extraction of 3D field)

## Synopsys

- Synopsys provides a physical model interface allowing to modify generation-recombination, mobility, band structure models etc
- implementation of more sophisticated models need support from the company
- direct contact to software developer/engineers not yet established

Contact other companies e.g. Global TCAD Solutions™?

Whatever the company, **build good relations with it!**



# Milestones & Deliverables

# DRD3

*S=short (3 years), M=Medium (6 years), L=Long (>> 6 years)*

*M=milestone D=deliverable*

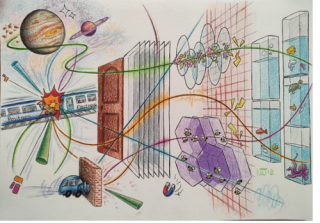
*Protocols to transfer electric field from TCAD to Allpix2 (~ ready but need to be validated to all sorts of structures maybe)*

*SM: Flexible CMOS simulation of 65 nm to test design variations in 1 year?*

*SM CCE vs fluence vs voltage for HL-LHC (depends on RD53C chip)*

*SD: Model for  $1e17$ ? (includes mobility models and more)*

*MM: TCAD for different WBS ?*



# Ressources

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# DRD3

FTEs: 5 in ~ 10 institutes

Licenses for this: ~ 50k€/year (+/- 50%)

